

## AMENDMENT(S) TO THE SPECIFICATION

Please replace the title with the following new title:

### POWER SEMICONDUCTOR DEVICE ASSEMBLY WITH INTEGRATED CURRENT SENSING AND CONTROL

Please replace the paragraph beginning at page 3, lines 14-21, with the following  
rewritten paragraph:

A<sup>1</sup> Device 20 has its bottom power electrode (drain) secured to conductive pad ~~20~~ 13 as by solder, or conductive epoxy or the like. The ~~drain~~ source may be suitably connected with a current carrying terminal conductor 30, which is a rigid, L-shaped thin, flat and copper bar which has its lower leg 31 soldered or connected by a conductive epoxy to pad 14 and is suitably arranged so that it carries the source to drain current of device 20. A plurality of parallel wire bonds 33, 34 connect the source electrode 35 (Figure 1) of MOSFET 20 to the upright leg 31 of current conductor 30.

Please replace the paragraph beginning at page 4, lines 15-25, with the following  
rewritten paragraph:

A<sup>2</sup> By placing the sensor 60, which is preferably a Hall effect element or a magneto resistive device (MRD), adjacent the edge 71, the Hall element will be in the path of and will intercept the magnetic field lines produced by the current in conductor 30, as shown in Figure 2. Details of the structure of the Hall effect element and MRD, including input and output terminals and biases are well known and are not described herein. The Hall element 60, or other sensor, will then produce an output voltage proportional to the field and thus to the current in conductor 30. This output signal can then be coupled back to the IC 46, as shown by dotted lines 80 in Figures 2 and 3 to effect a desired control of MOSFET 20 in response to its source to drain current. In addition to the described physical relative locations of the sensing device and the current carrying conductor, ~~There~~ there could be other locations.